

# MMBT9013DLT1

Preferred Device

## General Purpose Transistor

NPN Silicon

### Features

- Pb-Free Packages are Available

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CE0}$	40	Vdc
Collector-Base Voltage	$V_{CB0}$	80	Vdc
Emitter-Base Voltage	$V_{EB0}$	6.0	Vdc
Collector Current - Continuous	$I_C$	200	mA <sub>dc</sub>

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

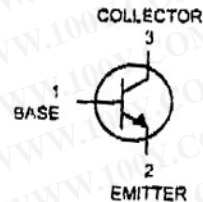
1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



ON Semiconductor

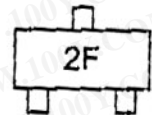
<http://onsemi.com>



### MARKING DIAGRAM



SOT-23 (TO-236)  
CASE 318  
Style G



2F = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping
MMBT9013DLT1	SOT-23	3000 / Tape & Reel
MMBT9013DLT1G	SOT-23	3000 / Tape & Reel
MMBT9013DLT3	SOT-23	10000 / Tape & Reel
MMBT9013DLT3G	SOT-23	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-34970699  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	-	Vdc
Collector-Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	60	-	Vdc
Emitter-Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	-	Vdc
Base Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{NL}$	-	50	nAdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{CEX}$	-	50	nAdc

**ON CHARACTERISTICS** (Note 3)

DC Current Gain ( $I_C = 0.1\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	40 70 100 60 30	- - 300 - -	-
Collector-Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{CE(sat)}$	- -	0.2 0.3	Vdc
Base-Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{BE(sat)}$	0.65 -	0.85 0.95	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	-	MHz
Output Capacitance ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	-	4.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	-	8.0	pF
Input Impedance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$Z_{ie}$	1.0	10	k ohms
Voltage Feedback Ratio ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$r_{re}$	0.5	8.0	$\times 10^{-4}$
Small-Signal Current Gain ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	100	400	-
Output Admittance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	1.0	40	$\mu\text{mhos}$
Noise Figure ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 100\text{ }\mu\text{Adc}$ , $R_S = 1.0\text{ k ohms}$ , $f = 1.0\text{ kHz}$ )	NF	-	5.0	dB

**SWITCHING CHARACTERISTICS**

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ , $I_C = 10\text{ mAdc}$ , $I_{B1} = 1.0\text{ mAdc}$ )	$t_d$	-	35	ns
Rise Time		$t_r$	-	35	
Storage Time	$(V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mAdc}$ , $I_{B1} = I_{B2} = 1.0\text{ mAdc}$ )	$t_s$	-	200	ns
Fall Time		$t_f$	-	50	

3 Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

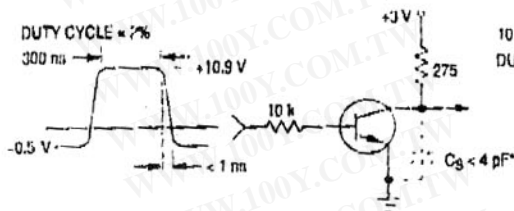


Figure 1. Delay and Rise Time Equivalent Test Circuit

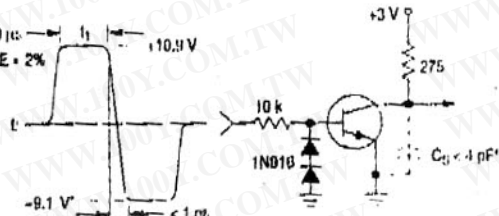


Figure 2. Storage and Fall Time Equivalent Test Circuit



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## TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$

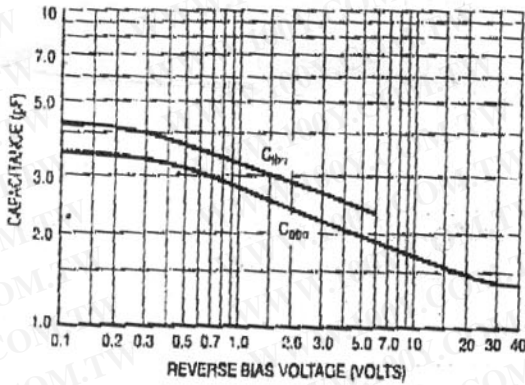


Figure 3. Capacitance

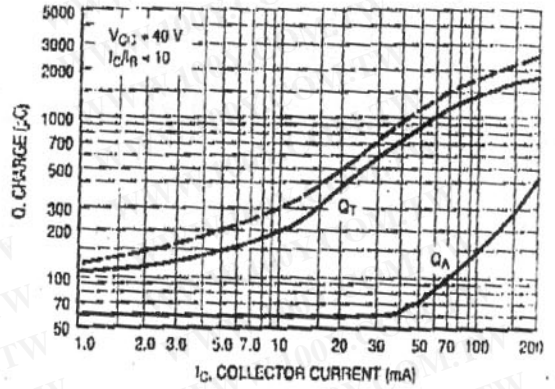


Figure 4. Charge Data

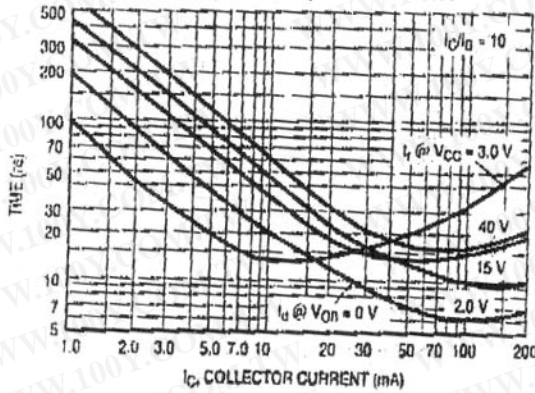


Figure 5. Turn-On Time

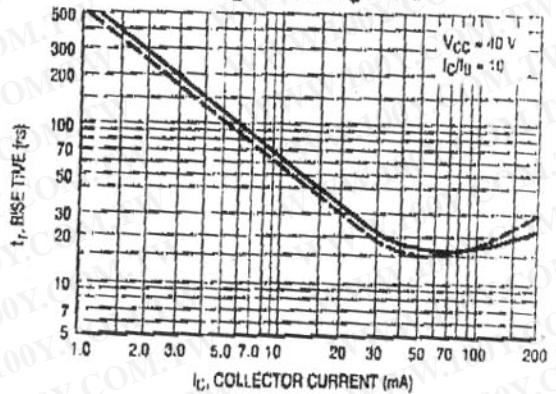


Figure 6. Rise Time

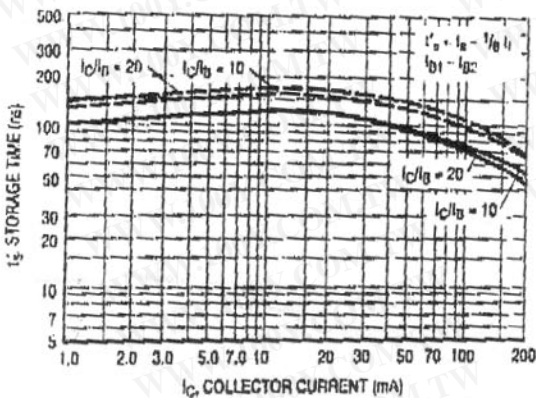


Figure 7. Storage Time

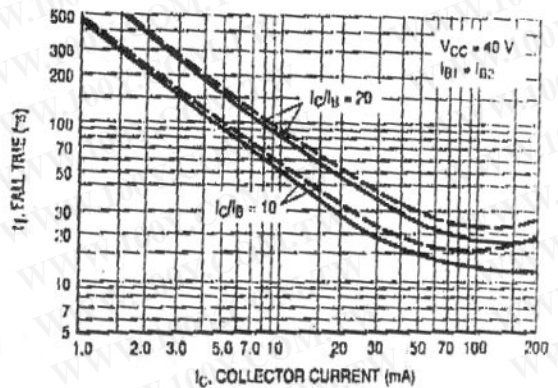


Figure 8. Fall Time

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